

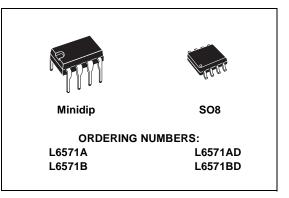
## L6571A L6571B HIGH VOLTAGE HALF BRIDGE DRIVER WITH OSCILLATOR

- HIGH VOLTAGE RAIL UP TO 600V
- BCD OFF LINE TECHNOLOGY
- 15.6V ZENER CLAMP ON V<sub>S</sub>
- DRIVER CURRENT CAPABILITY:
  SINK CURRENT = 270mA
  SOURCE CURRENT = 170mA
- VERY LOW START UP CURRENT: 150µA
- UNDER VOLTAGE LOCKOUT WITH HYSTERESIS
- PROGRAMMABLE OSCILLATOR FREQUENCY
- DEAD TIME 1.25µs (L6571A) or 0.72µs (L6571B)
- dV/dt IMMUNITY UP TO ±50V/ns
- ESD PROTECTION

### DESCRIPTION

The device is a high voltage half bridge driver with built in oscillator. The frequency of the oscillator can be programmed using external resistor and capaci-

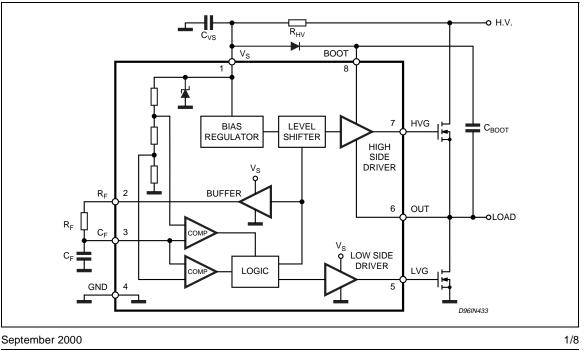
### **BLOCK DIAGRAM**



tor. The internal circuitry of the device allows it to be driven also by external logic signal.

The output drivers are designed to drive external nchannel power MOSFET and IGBT. The internal logic assures a dead time to avoid cross-conduction of the power devices.

Two version are available: L6571A and L6571B. They differ in the internal dead time:  $1.25\mu$ s and  $0.72\mu$ s (typ.)



### L6571A L6571B

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
I <sub>S</sub> (*)	Supply Current	25	mA
$V_{CF}$	Oscillator Resistor Voltage	18	V
V <sub>LVG</sub>	Low Side Switch Gate Output	14.6	V
Vout	High Side Switch Source Output	-1 to V <sub>BOOT</sub> - 18	V
V <sub>HVG</sub>	High Side Switch Gate Output	-1 to V <sub>BOOT</sub>	V
V <sub>BOOT</sub>	Floating Supply Voltage	618	V
V <sub>BOOT/OUT</sub>	Floating Supply vs OUT Voltage	18	V
dV <sub>BOOT</sub> /dt	VBOOT Slew Rate (Repetitive)	± 50	V/ns
dV <sub>OUT</sub> /dt	VOUT Slew Rate (Repetitive)	± 50	V/ns
T <sub>stg</sub>	Storage Temperature	-40 to 150	°C
Тj	Junction Temperature	-40 to 150	°C
Tamb	Ambient Temperature (Operative)	-40 to 125	°C

(\*) The device has an internal zener clamp between GND and VS (typical 15.6V). Therefore the circuit should not be driven by a DC low impedance power source. Note: ESD immunity for pins 6, 7 and 8 is guaranteed up to 900 V (Human Body Model)

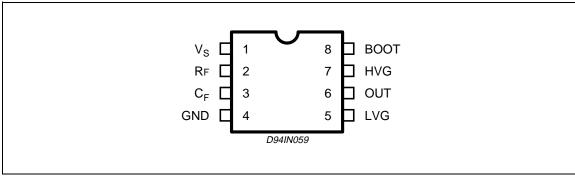
### THERMAL DATA

Symbol	Parameter	Minidip	SO8	Unit
R <sub>th j-amb</sub>	Thermal Resistance Junction-Ambient Max	100	150	°C/W

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min.	Max.	Unit
Vs	Supply Voltage	10	V <sub>CL</sub>	V
VBOOT	Floating Supply Voltage	-	500	V
V <sub>OUT</sub>	High Side Switch Source Output	-1	V <sub>BOOT</sub> -V <sub>CL</sub>	V
f <sub>out</sub>	Oscillation Frequency		200	kHz

### **PIN CONNECTION**



57

2/8

PIN	FU	INC.	TION
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N°	Pin	Description
1	VS	Supply input voltage with internal clamp [typ. 15.6V]
2	RF	Oscillator timing resistor pin. A buffer set alternatively to $V_S$ and GND can provide current to the external resistor RF connected between pin 2 and 3. Alternatively, the signal on pin 2 can be used also to drive another IC (i.e. another L6569/71 to drive a full H-bridge)
3	CF	Oscillator timing capacitor pin. A capacitor connected between this pin and GND fixes (together with R <sub>F</sub> ) the oscillating frequency Alternatively an external logic signal can be applied to the pin to drive the IC.
4	GND	Ground
5	LVG	Low side driver output. The output stage can deliver 170mA source and 270mA sink [typ.values].
6	OUT	Upper driver floating reference
7	HVG	High side driver output. The output stage can deliver 170mA source and 270mA sink [typ.values].
8	BOOT	Bootstrap voltage supply. It is the upper driver floating supply.

### $\textbf{ELECTRICAL CHARACTERISTCS} (V_S = 12V; V_{BOOT} - V_{OUT} = 12V; T_j = 25^{\circ}C; \text{ unless otherwise specified.})$

Symbol	Pin	Parameter	Test Condition	Min.	Тур.	Max.	Unit
V <sub>SUVP</sub>	1	VS Turn On Threshold		8.3	9	9.7	V
V <sub>SUVN</sub>		VS Turn Off Threshold		7.3	8	8.7	V
V <sub>SUVH</sub>		VS Hysteresis		0.7	1	1.3	V
V <sub>CL</sub>		VS Clamping Voltage	I <sub>S</sub> = 5mA	14.6	15.6	16.6	V
I <sub>SU</sub>		Start Up Current	$V_{\rm S} < V_{\rm SUVN}$		150	250	μΑ
Ιq		Quiescent Current	$V_{S} > V_{SUVP}$		500	700	μΑ
IBOOTLK	8	Leakage Current BOOT pin vs GND	V <sub>BOOT</sub> = 580V			5	μA
IOUTLK	6	Leakage Current OUT pin vs GND	V <sub>OUT</sub> = 562V			5	μA
I <sub>HVG</sub> so	7	High Side Driver Source Current	V <sub>HVG</sub> = 6V	110	175		mA
I <sub>HVG</sub> SI		High Side Driver Sink Current	V <sub>HVG</sub> = 6V	190	275		mA
ILVG SO	5	Low Side Driver Source Current	$V_{LVG} = 6V$	110	175		mA
ILVG SI		Low Side Driver Sink Current	$V_{LVG} = 6V$	190	275		mA
V <sub>RFO</sub> N	2	RF High Level Output Voltage	I <sub>RF</sub> = 1mA	V <sub>S</sub> -0.05		V <sub>S</sub> -0.2	V
V <sub>RF</sub> OFF		RF Low Level Output Voltage	I <sub>RF</sub> = -1mA	50		200	mV
V <sub>CFU</sub>	3	CF Upper Threshold		7.7	8	8.2	V
V <sub>CFL</sub>		CF Lower Threshold		3.80	4	4.3	V
t <sub>d</sub>		Internal Dead Time	L6571A L6571B	0.85 0.50	1.25 0.72	1.65 0.94	μs μs

Symbol	Pin	Parameter	Test Condition	Min.	Тур.	Max.	Unit
DC		Duty Cycle, Ratio Between Dead Time + Conduction Time of High Side and Low Side Drivers		0.45	0.5	0.55	
I <sub>AVE</sub>	1	Average Current from Vs	No Load, fs = 60KHz		1.2	1.5	mA
f <sub>out</sub>	6	Oscillation Frequency	$R_{T} = 12K; C_{T} = 1nF$	57	60	63	kHz

### ELECTRICAL CHARACTERISTCS (continued)

### **OSCILLATOR FREQUENCY**

The frequency of the internal oscillator can be programmed using external resistor and capacitor.

The nominal oscillator frequency can be calculated using the following equation:

$$f_{OSC} = \frac{1}{2 \cdot R_F \cdot C_F \cdot In2} = \frac{1}{1.3863 \cdot R_F \cdot C_F}$$

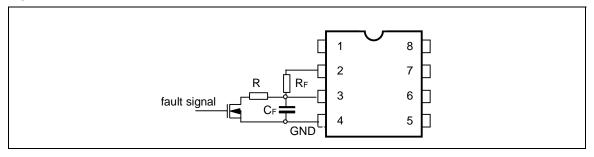
Where R<sub>F</sub> and C<sub>F</sub> are the external resistor and capacitor.

The device can be driven in "shut down" condition keeping the  $C_F$  pin close to GND, but some cares have to be taken:

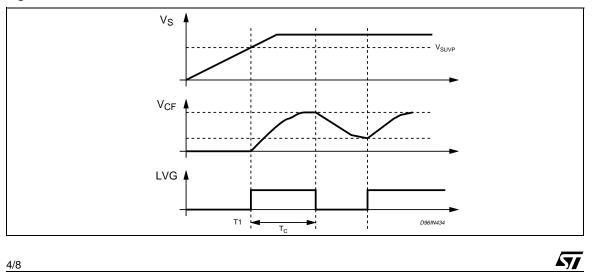
1. When  $C_F$  is to GND the high side driver is off and the low side is on

2. The forced discharge of the oscillator capacitor  $C_F$  must not be shorter than 1us: a simple way to do this is to limit the current discharge with a resistive path imposing  $R \cdot C_F > 1\mu s$  (see fig.1)

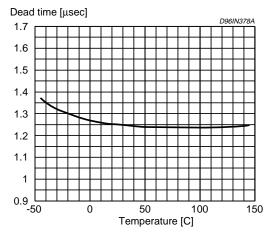
### Figure 1.

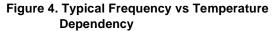


### Figure 2. Waveforms



# Figure 3. Typical Dead Time vs. Temperature Dependency (L6571A)





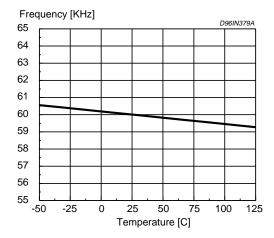
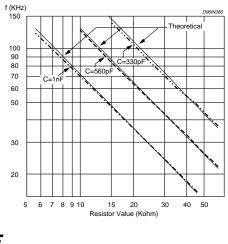
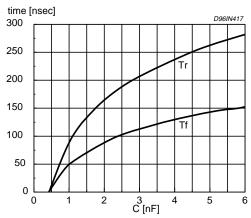


Figure 5. Typical and Theoretical Oscillator Frequency vs Resistor Value



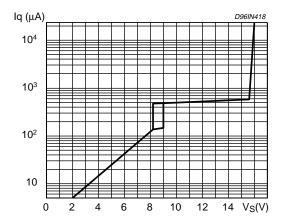
57

Figure 6. Typical Rise and Fall Times vs. Load Capacitance



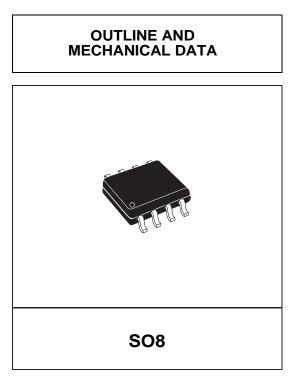
For both high and low side buffers  $@25^\circ\text{C}$  Tamb

Figure 7. Quiescent Current vs. Supply Voltage.

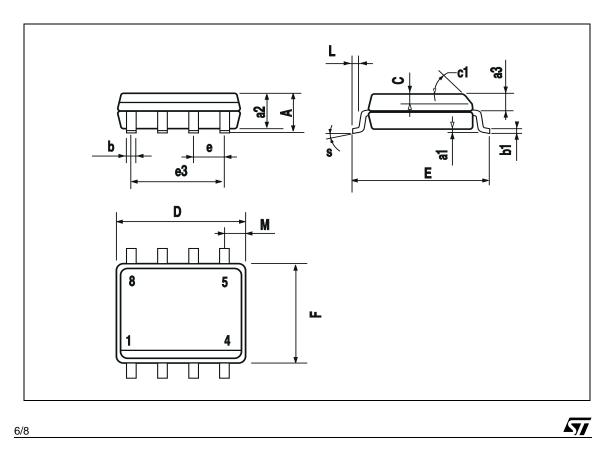


### L6571A L6571B

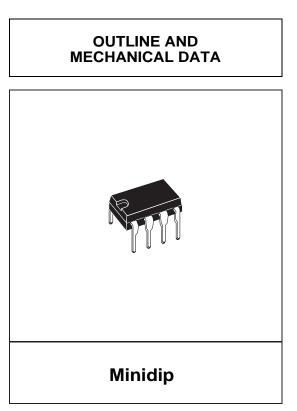
DIM.		mm			inch		
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			1.75			0.069	
a1	0.1		0.25	0.004		0.010	
a2			1.65			0.065	
a3	0.65		0.85	0.026		0.033	
b	0.35		0.48	0.014		0.019	
b1	0.19		0.25	0.007		0.010	
С	0.25		0.5	0.010		0.020	
c1			45° (	(typ.)			
D (1)	4.8		5.0	0.189		0.197	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		3.81			0.150		
F (1)	3.8		4.0	0.15		0.157	
L	0.4		1.27	0.016		0.050	
М			0.6			0.024	
S	8° (max.)						

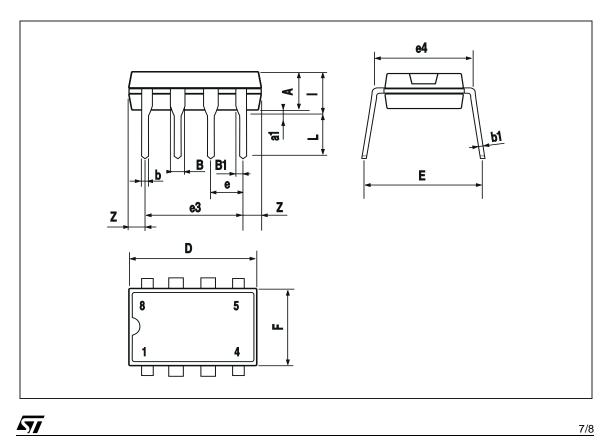


(1) D and F do not include mold flash or protrusions. Mold flash or potrusions shall not exceed 0.15mm (.006inch).



DIM.		mm			inch		
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А		3.32			0.131		
a1	0.51			0.020			
В	1.15		1.65	0.045		0.065	
b	0.356		0.55	0.014		0.022	
b1	0.204		0.304	0.008		0.012	
D			10.92			0.430	
Е	7.95		9.75	0.313		0.384	
е		2.54			0.100		
e3		7.62			0.300		
e4		7.62			0.300		
F			6.6			0.260	
I			5.08			0.200	
L	3.18		3.81	0.125		0.150	
Z			1.52			0.060	





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8/8